

# Product Specification

XBLW AOD4184

N-Channel Enhancement Mode MOSFET

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## Description

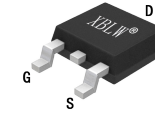
The AOD4184 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

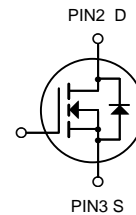
- $V_{DS} = 40V$   $I_D = 60A$
- $R_{DS(ON)} < 8.5m\Omega$  @  $V_{GS}=10V$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply



TO-252-2L



N-Channel MOSFET

## Package Marking and Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW AOD4184	TO-252-2L	AOD4184	Tape	2500Pcs/Reel

## Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	45	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	220	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	416.1	mJ
$I_{AS}$	Avalanche Current	39	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	64.6	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	2.8	°C/W

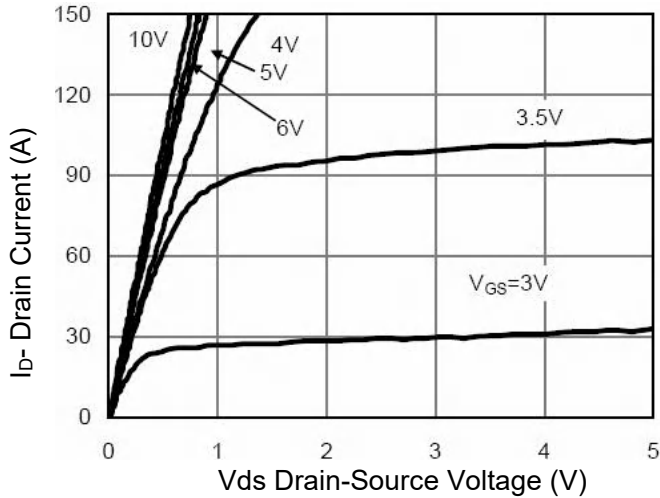
**Electrical Characteristics (TC=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	45	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	7.0	8.5	m $\Omega$
		$V_{GS}=4.5V, I_D=20A$		15	18	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=20A$	15	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	1800	-	PF
Output Capacitance	$C_{oss}$		-	280	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	190	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=2A, R_L=1\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	6.4	-	nS
Turn-on Rise Time	$t_r$		-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29.6	-	nS
Turn-Off Fall Time	$t_f$		-	16.8	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	29		nC
Gate-Source Charge	$Q_{gs}$		-	4.5		nC
Gate-Drain Charge	$Q_{gd}$		-	6.4		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=10A$	-		1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	68	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ C, I_F = 20A$ $di/dt = 100A/\mu s$ (Note 3)	-	29	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	26	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

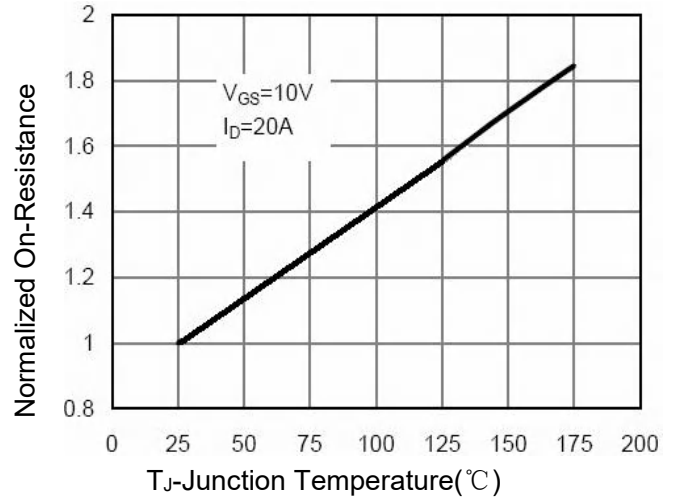
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $E_{AS}$  condition :  $T_J=25^\circ C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega$ .

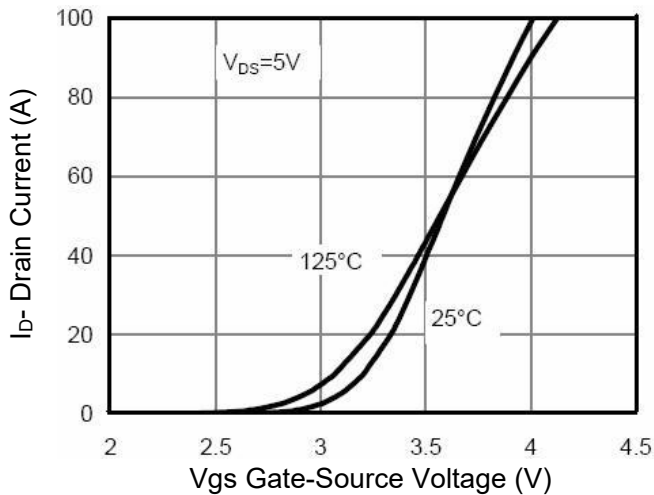
**Typical Electrical and Thermal Characteristics (Curves)**



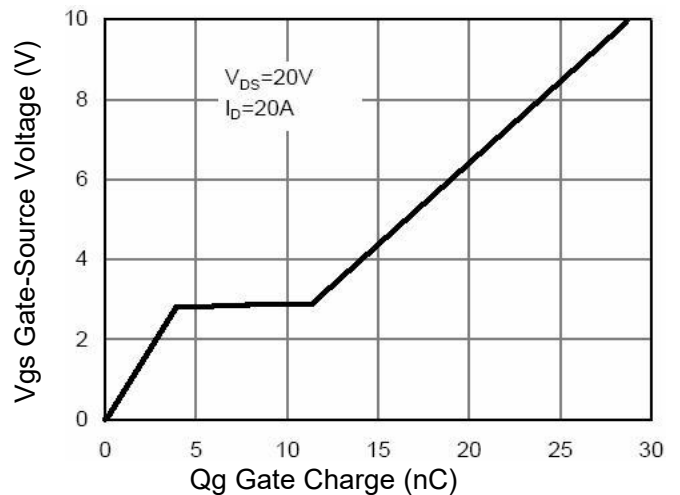
**Figure 1 Output Characteristics**



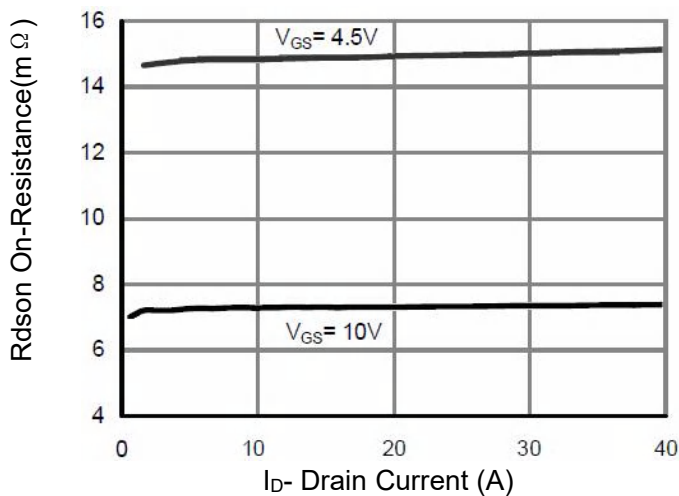
**Figure 4 Rdson-Junction Temperature**



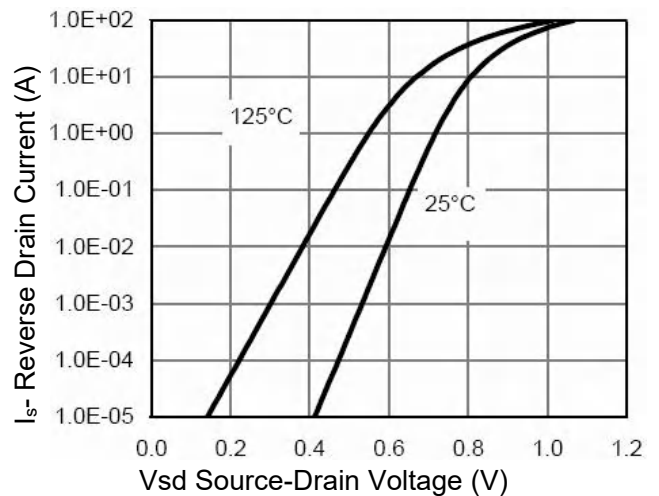
**Figure 2 Transfer Characteristics**



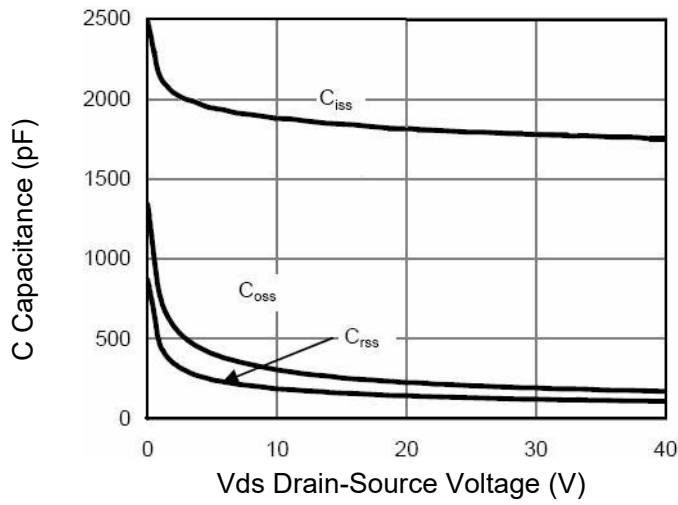
**Figure 5 Gate Charge**



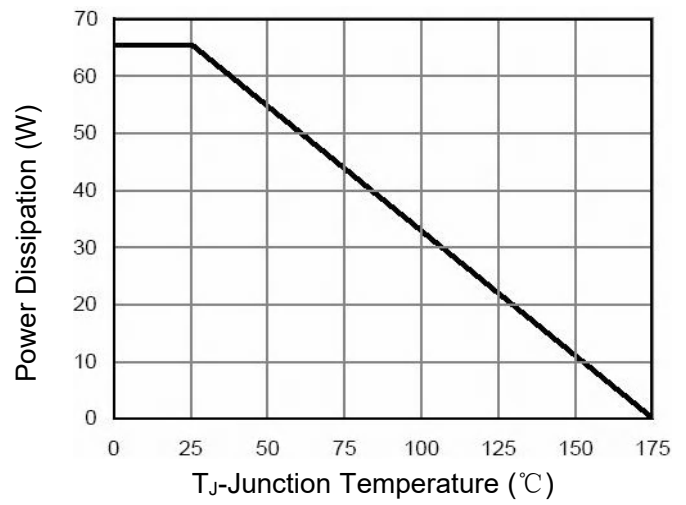
**Figure 3 Rdson- Drain Current**



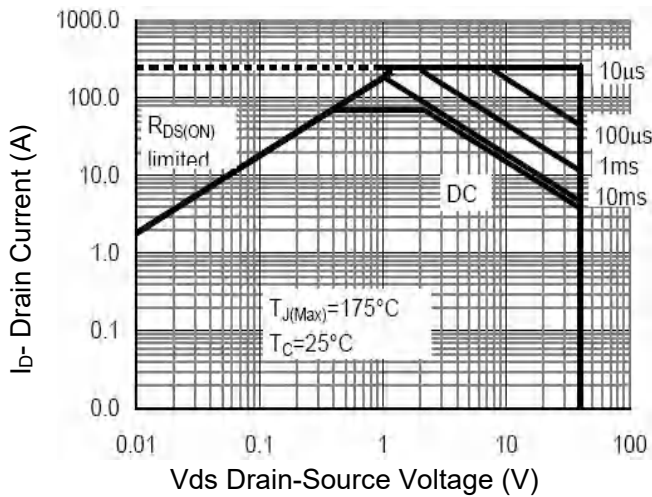
**Figure 6 Source- Drain Diode Forward**



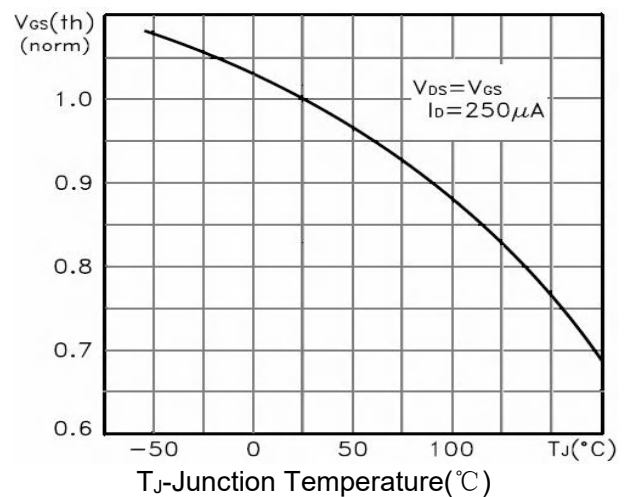
**Figure 7 Capacitance vs Vds**



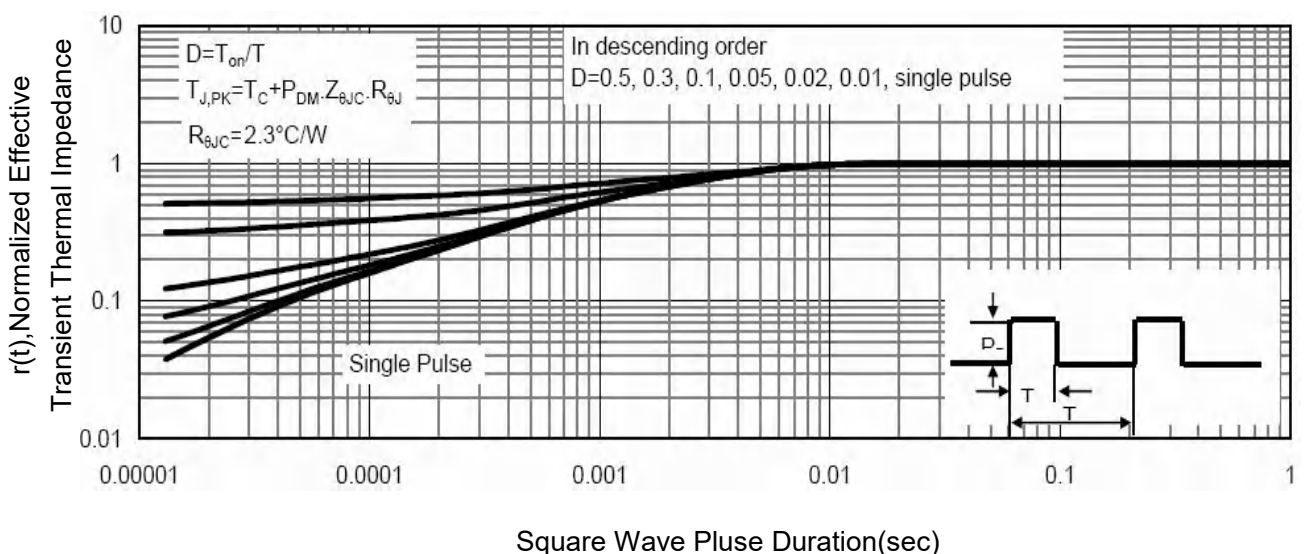
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



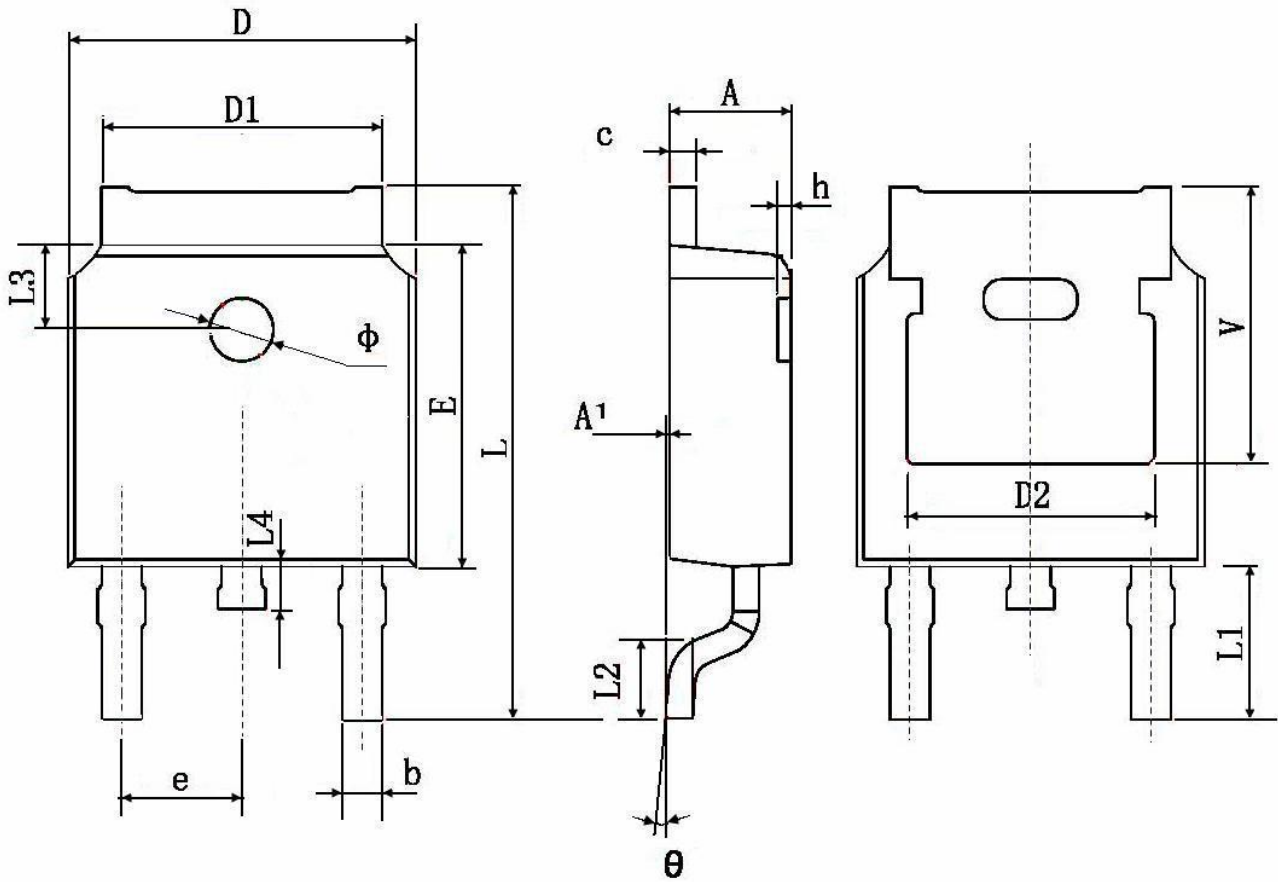
**Figure 10  $V_{GS(th)}$  vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**Package Information**

**TO-252**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
v	5.350 TYP.		0.211 TYP.	

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